

AMENDMENTS

This listing of claims will replace all prior versions, and listings, of claims in the application:

In the Claims

AI Claim 1 (currently amended): A semiconductor light-emitting device comprising:

a semiconductor light-emitting device chip including a chip substrate and a stack formed of semiconductor layers stacked on a surface of said chip substrate; and

a mount member having a mount surface, wherein

said semiconductor light-emitting device chip is connected to the mount surface of said mount member by solder between the semiconductor light-emitting device chip and said mount surface of said mount member, with said stack facing said mount surface, and

said mount member includes a material higher in thermal expansion coefficient than a material for said chip substrate.


Claim 2 (currently amended): A semiconductor light-emitting device comprising:

a semiconductor light-emitting device chip including a chip substrate and a stack formed of semiconductor layers stacked on a surface of said chip substrate; and

a mount member having a mount surface, wherein

said semiconductor light-emitting device chip is connected to the mount surface of said mount member by solder between the semiconductor light-emitting device chip and said mount surface of said mount member, with said stack facing said mount surface, and

said mount surface is curved to protrude and said semiconductor light-emitting device chip is curved along and connected to said mount surface.

 Claim 3 (original): The semiconductor light-emitting device according to claim 1, wherein
said chip substrate includes nitride-based compound semiconductor and said stack
includes nitride-based compound semiconductor.

Claim 4 (original): The semiconductor light-emitting device according to claim 3, wherein
said mount member includes at least one of iron and copper.

Claim 5 (original): The semiconductor light-emitting device according to claim 1, wherein
said mount surface and said stack are connected by solder and said solder includes at
least one selected from the group consisting of In, Sn, Pb and Au.

Claim 6 (new): The semiconductor light-emitting device according to claim 5, wherein
said chip substrate includes nitride-based compound semiconductor and said stack
includes nitride-based compound semiconductor.

Claim 7 (new): The semiconductor light-emitting device according to claim 6, wherein
said mount member includes at least one of iron and copper.

Claim 8 (new): The semiconductor light-emitting device according to claim 2, wherein
said chip substrate includes nitride-based compound semiconductor and said stack
includes nitride-based compound semiconductor.

Claim 9 (new): The semiconductor light-emitting device according to claim 8, wherein
said mount member includes at least one of iron and copper.

Claim 10 (new): A semiconductor light-emitting device comprising:

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a semiconductor light-emitting device chip including a chip substrate and a stack formed of semiconductor layers stacked on a surface of said chip substrate; and

a mount member having a mount surface, wherein

said semiconductor light-emitting device chip is connected to the mount surface of said mount member by solder between the semiconductor light-emitting device chip and said mount surface of said mount member, with said stack facing said mount surface,

said mount member includes a material higher in thermal expansion coefficient than a material for said chip substrate; and

said stack is formed by stacking the semiconductor layers on the surface of said chip substrate in advance of connecting said semiconductor light-emitting device chip to the mount surface of said mount member.

Claim 11 (new): The semiconductor light-emitting device according to claim 10, wherein

said chip substrate includes nitride-based compound semiconductor and said stack includes nitride-based compound semiconductor.

Claim 12 (new): The semiconductor light-emitting device according to claim 11, wherein

said mount member includes at least one of iron and copper.

Claim 13 (new): A semiconductor light-emitting device comprising:

a semiconductor light-emitting device chip including a chip substrate and a stack formed of semiconductor layers stacked on a surface of said chip substrate; and

a mount member having a mount surface, wherein

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said semiconductor light-emitting device chip is connected to the mount surface of said mount member by solder between the semiconductor light-emitting device chip and said mount surface of said mount member, with said stack facing said mount surface,

said mount surface is curved to protrude and said semiconductor light-emitting device chip is curved along and connected to said mount surface, and

said stack is formed by stacking the semiconductor layers on the surface of said chip substrate in advance of connecting said semiconductor light-emitting device chip to the mount surface of said mount member.

Claim 14 (new): The semiconductor light-emitting device according to claim 13, wherein

said chip substrate includes nitride-based compound semiconductor and said stack includes nitride-based compound semiconductor.

Claim 15 (new): The semiconductor light-emitting device according to claim 14, wherein

said mount member includes at least one of iron and copper.

Claim 16 (new): A semiconductor light-emitting device comprising:

a semiconductor light-emitting device chip including a chip substrate and a stack formed of semiconductor layers stacked on a surface of said chip substrate; and

a mount member having a mount surface, wherein

said semiconductor light-emitting device chip is connected to the mount surface of said mount member with said stack facing said mount surface, and

said mount member includes a material higher in thermal expansion coefficient than a material for said chip substrate,

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wherein said mount surface and said stack are connected by solder and said solder includes at least one selected from the group consisting of In, Sn, Pb and Au.

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Claim 17 (new): The semiconductor light-emitting device according to claim 16, wherein

said chip substrate includes nitride-based compound semiconductor and said stack includes nitride-based compound semiconductor.

Claim 18 (new): The semiconductor light-emitting device according to claim 17, wherein

said mount member includes at least one of iron and copper.
